

# BDW94CF PNP Epitaxial Silicon Transistor

# **Power Linear and Switching Application**

- · Power Darlington TR
- · Complement to BDW93CF Respectively



# Absolute Maximum Ratings T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	-100	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-100	V
I <sub>C</sub>	Collector Current (DC)	-12	А
I <sub>CP</sub>	Collector Current (Pulse) *	-15	А
I <sub>B</sub>	Base Current	-0.2	А
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> = 25°C)	30	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-65 ~ 150	°C

### Electrical Characteristics T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Тур.	Max	Units
V <sub>CEO(sus)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> -100mA, I <sub>B</sub> = 0	-100			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = -100V, I <sub>E</sub> = 0			-100	μΑ
I <sub>CEO</sub>	Collector Cut-off Current	VV <sub>CE</sub> = -100V, I <sub>B</sub> = 0			-1	mA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = -5V, I_{C} = 0$			-2	mA
h <sub>FE</sub>	DC Current Gain *	$V_{CE} = -3V$ , $I_{C} = -3A$ $V_{CE} = -3V$ , $I_{C} = -5A$ $V_{CE} = -3V$ , $I_{C} = -10A$	1000 750 100		20000	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage *	I <sub>C</sub> = -5A, I <sub>B</sub> = -20mA I <sub>C</sub> = -10A, I <sub>B</sub> = -100mA			-2 -3	V V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage *	I <sub>C</sub> = -5A, I <sub>B</sub> = -20mA I <sub>C</sub> = -10A, I <sub>B</sub> = -100mA			-2.5 -4	V V
V <sub>F</sub>	Parallel Diode Forward Voltage *	I <sub>F</sub> = -5A I <sub>F</sub> = -10A		-1.3 -1.8	-2 -4	V V

<sup>\*</sup> Pulse Test: PW =  $300\mu s$ , Duty Cycle = 1.5% Pulsed

# **Package Marking and Ordering Information**

<b>Device Marking</b>	Device	Package	Reel Size	Tape Width	Quantity
BDW94CF	BDW94CF	TO-220F	-	-	50

# **Typical Performance Characteristics**

Figure 1. DC Current Gain

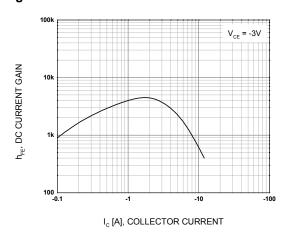


Figure 2. Collector-Emitter Saturation Voltage

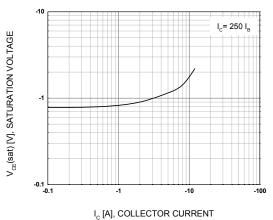


Figure 3. Base-Emitter On Voltage

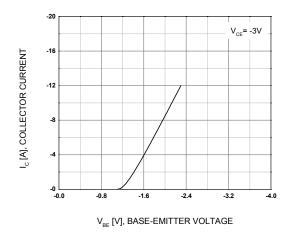
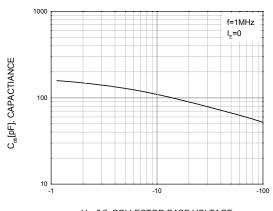


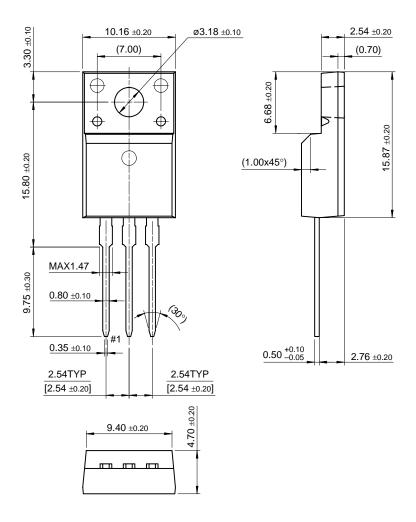
Figure 4. Output Capacitance



 $V_{CB}$  [V], COLLECTOR-BASE VOLTAGE

# **Mechanical Dimensions**

# TO-220F



Dimensions in Millimeters

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### **PRODUCT STATUS DEFINITIONS**

### **Definition of Terms**

Datasheet Identification	Product Status	Definition
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